

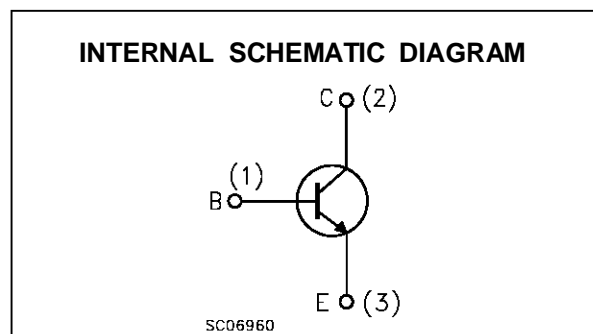
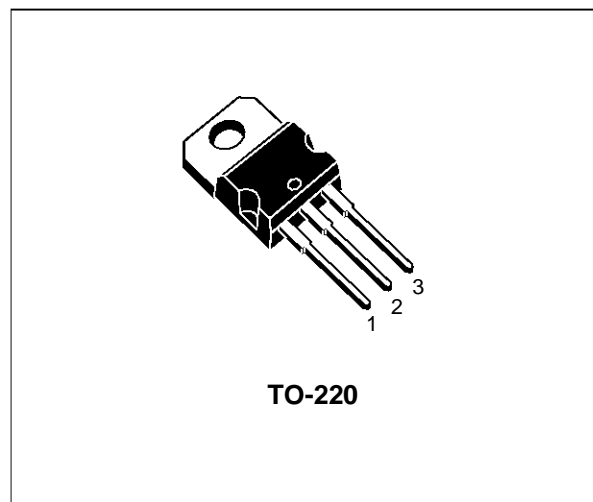
SILICON NPN TRANSISTOR

■ SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The D44H8, and D44H11 are silicon multiepitaxial planar NPN transistors mounted in Jedec TO-220 plastic package.

They are intended for various switching and general purpose applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		D44H8	D44H11	
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	60	80	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	5		V
I _C	Collector Current	10		A
I _{CM}	Collector Peak Current	20		A
P _{tot}	Total Dissipation at T _c ≤ 25 °C	50		W
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

D44H8/D44H11

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	2.5	$^{\circ}C/W$
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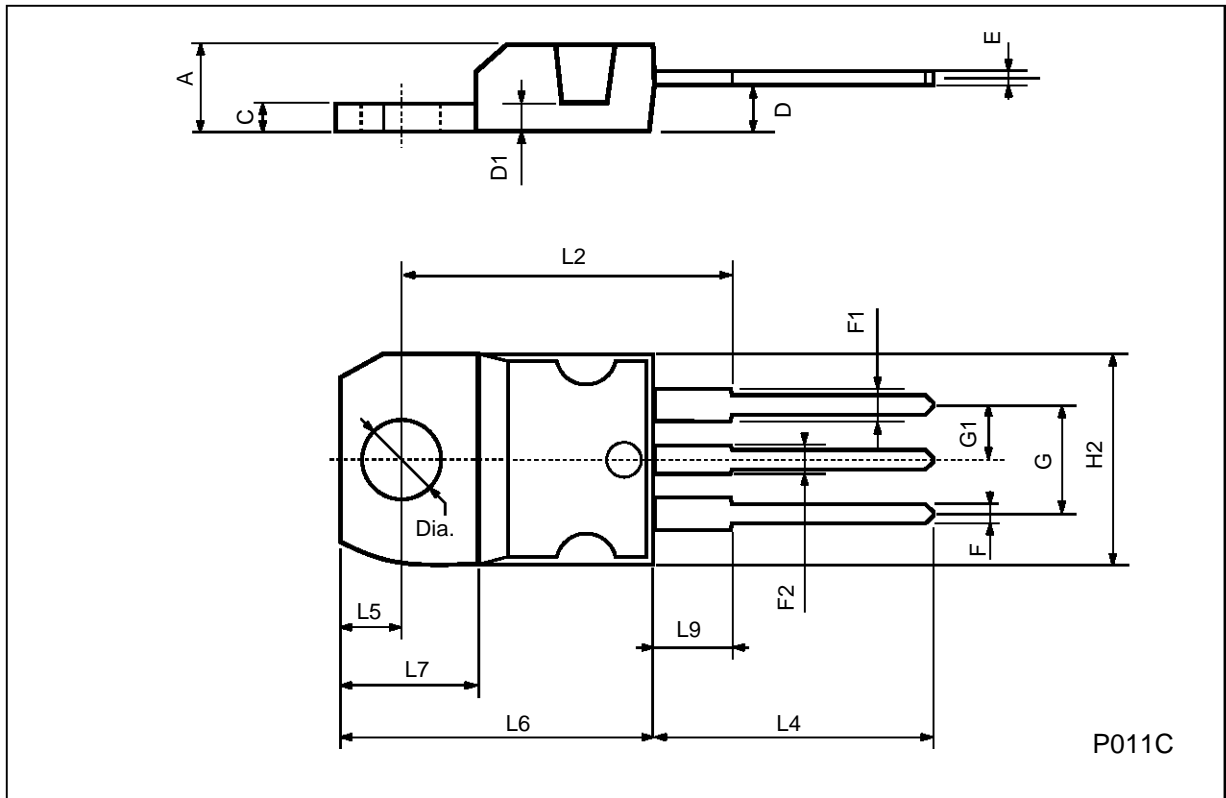
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = \text{rated } V_{CEO}$			10	μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5V$			100	μA
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage	$I_C = 100 \text{ mA}$ for D44H8 for D44H11	60 80			V V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 8 \text{ A}$ $I_B = 0.4 \text{ A}$			1	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 8 \text{ A}$ $I_B = 0.8 \text{ A}$			1.5	V
h_{FE}^*	DC Current Gain	$I_C = 2 \text{ A}$ $V_{CE} = 1 \text{ V}$ $I_C = 4 \text{ A}$ $V_{CE} = 1 \text{ V}$	60 40			

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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